



60V N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI3333-8 (TYPE UX)

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C
	16mΩ @ V _{GS} = 10V	35A
60V	22mΩ @ V _{GS} = 4.5V	28A

Features and Benefits

- Low R_{DS(ON)} Ensures On-State Losses are Minimized
- Small Form Factor Thermally Efficient Package Enables Higher **Density End Products**
- Occupies just 33% of the Board Area Occupied by SO-8 Enabling Smaller End Product
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}), yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Motor Control
- DC-DC Converters
- Power Management

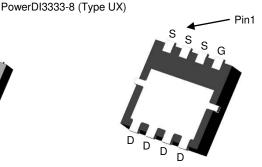
Mechanical Data

- Case: PowerDI[®]3333-8 (Type UX)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.072 grams (Approximate)

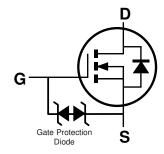




Top View



Bottom View



Internal Schematic

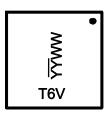
Ordering Information (Note 4)

Part Number	Case	Packaging
DMT6015LFV-7	PowerDI3333-8 (Type UX)	2,000/Tape & Reel
DMT6015LFV-13	PowerDI3333-8 (Type UX)	3,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See http://www.diodes.com/quality/lead_free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



T6V= Product Type Marking Code YYWW = Date Code Marking \overline{YY} = Last Two Digits of Year (ex: 18 = 2018) WW = Week Code (01 to 53)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V_{DSS}	60	V	
Gate-Source Voltage		V_{GSS}	±16	V
	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	ΙD	9.5 7.6	Α
Continuous Drain Current (Note 5) V _{GS} = 10V	$T_C = +25$ °C $T_C = +100$ °C	Ι _D	35 22	Α
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	60	Α	
Maximum Continuous Body Diode Forward Current (Note 5)	Is	2	Α	
Pulsed Body Diode Forward Current (10μs Pulse, Duty Cycle = 1%)		I _{SM}	60	Α
Avalanche Current, L = 0.1mH		I _{AS}	17	Α
Avalanche Energy, L = 0.1mH		E _{AS}	14.5	mJ
V_{DS} Spike $t = 10 \mu s$		V _{SPIKE}	75	V

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)	$T_A = +25^{\circ}C$	٦	2.2	W
Total Power Dissipation (Note 5)	$T_C = +25$ °C	P _D	30	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	D	57	°C/W
Thermal nesistance, bunction to Ambient (Note 5)	t<10s	$R_{\theta JA}$	35	
Thermal Resistance, Junction to Case (Note 5)	$R_{ heta JC}$	4.2		
Operating and Storage Temperature Range		$T_{J_i} T_{STG}$	-55 to +150	°C

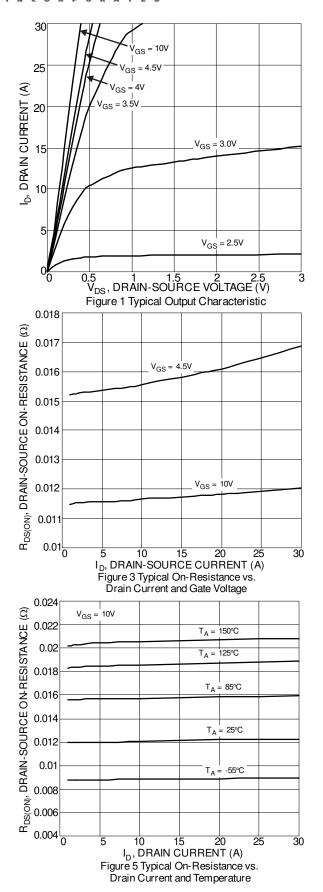
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

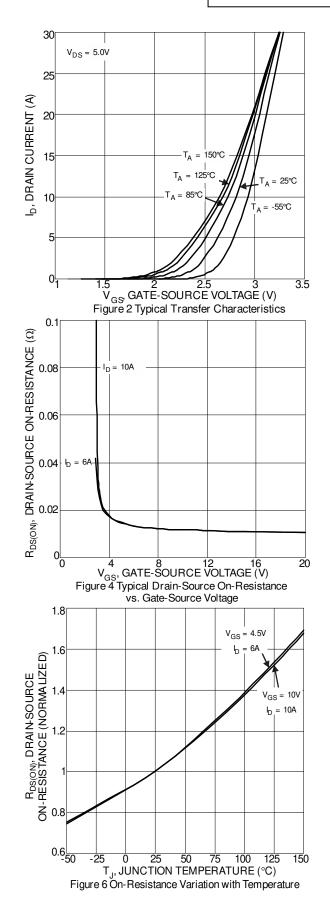
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 6)							
Drain-Source Breakdown Voltage	BV _{DSS}	60	_	_	٧	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μΑ	$V_{DS} = 48V$, $V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±10	μΑ	$V_{GS} = \pm 16V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 6)							
Gate Threshold Voltage	V _{GS(TH)}	0.5	_	2.5	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
Static Drain-Source On-Resistance	D	_	11.7	16	mΩ	$V_{GS} = 10V, I_D = 10A$	
Static Dialii-Source Off-Nesistance	R _{DS(ON)}	_	15.7	22	11177	$V_{GS} = 4.5V, I_D = 6A$	
Diode Forward Voltage	V_{SD}		0.7	1.2	V	$V_{GS} = 0V$, $I_S = 1A$	
DYNAMIC CHARACTERISTICS (Note 7)							
Input Capacitance	C _{iss}	_	1103	_	pF	V 20V V 0V	
Output Capacitance	Coss	_	251	_	pF	V _{DS} = 30V, V _{GS} = 0V, - f = 1MHz	
Reverse Transfer Capacitance	Crss	-	20	_	pF	1 = TIVITIZ	
Gate Resistance	R_g	_	1.5		Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Q_g	1	8.9		nC		
Total Gate Charge (V _{GS} = 10V)	Q_g	_	18.9	_	nC	V _{DS} = 30V. I _D = 10A	
Gate-Source Charge	Q_{gs}	1	3		nC	$\int_{0}^{\infty} V_{DS} = 30V, ID = 10A$	
Gate-Drain Charge	Q_{gd}	_	2.8	_	nC	1	
Turn-On Delay Time	t _{D(ON)}	_	4.1	_	ns	$V_{GS} = 10V, V_{DS} = 30V,$ $R_g = 6\Omega, I_D = 10A$	
Turn-On Rise Time	t _R	_	7.1	_	ns		
Turn-Off Delay Time	t _{D(OFF)}	_	19.5	_	ns		
Turn-Off Fall Time	t _F	_	8.6	_	ns		
Body Diode Reverse Recovery Time	t _{RR}	_	21.2	_	ns	I _F = 10A, di/dt = 100A/μs	
Body Diode Reverse Recovery Charge	Q _{RR}		13.2	_	nC		

5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate. Notes:

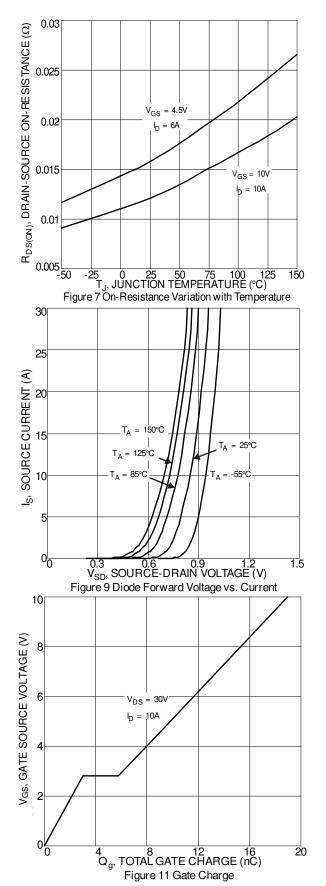
Short duration pulse test used to minimize self-heating effect.
Guaranteed by design. Not subject to product testing.

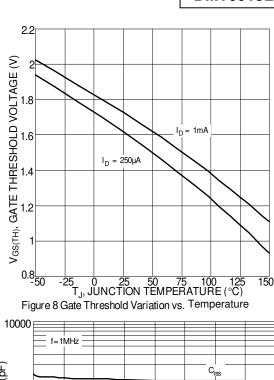


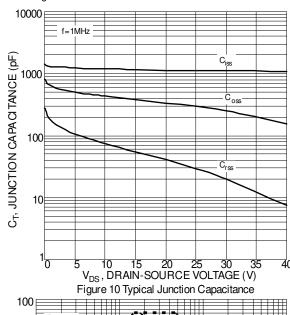


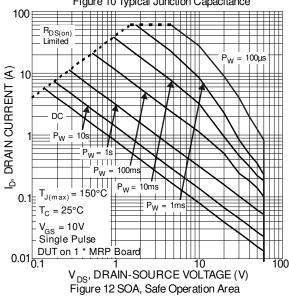




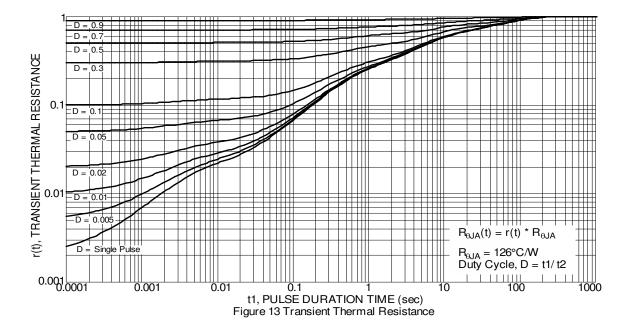










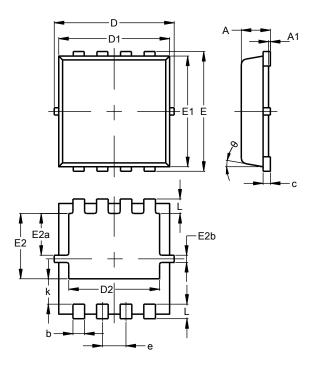




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (Type UX)

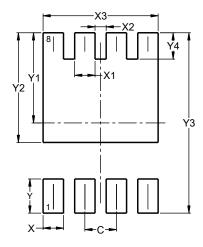


PowerDI3333-8 (Type UX)				
Dim	Min Max Typ			
Α	0.75	0.85	0.80	
A1	0.00	0.05		
b	0.25	0.40	0.32	
С	0.10	0.25	0.15	
D	3.20	3.40	3.30	
D1	2.95	3.15	3.05	
D2	2.30	2.70	2.50	
Е	3.20	3.40	3.30	
E1	2.95	3.15	3.05	
E2	1.60	2.00	1.80	
E2a	0.95	1.35	1.15	
E2b	0.10	0.30	0.20	
е	0.65 BSC			
k	0.50	0.90	0.70	
L	0.30	0.50	0.40	
θ	0°	12°	10°	
All Dimensions in mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (Type UX)



Dimensions	Value (in mm)
С	0.650
X	0.420
X1	0.420
X2	0.230
Х3	2.370
Υ	0.700
Y1	1.850
Y2	2.250
Y3	3.700
Y4	0.540



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